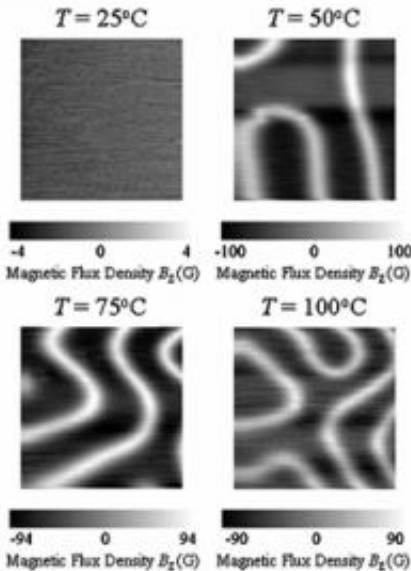
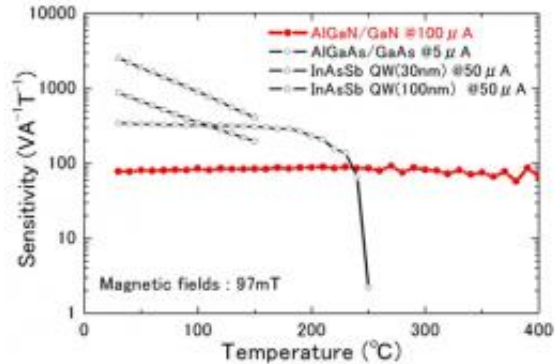


Hall effect magnetic field sensors for high temperatures and harmful radiation environments

22 March 2012, By Adarsh Sandhu



SHPM images of a bismuth substituted iron garnet thin film at 25-100 °C under an external perpendicular magnetic field of 150 Oe. Credit: Toyohashi University of Technology



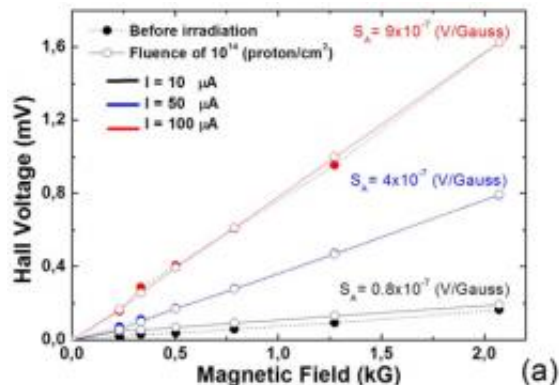
Temperature dependence of current-related magnetic sensitivity. Credit: Toyohashi University of Technology

To resolve these issues, the Toyohashi Tech researchers used AlGaIn/GaN two-dimensional electron gas heterostructures to fabricate high sensitivity micro-Hall effect [magnetic field sensors](#) that are stable at high temperatures and high fluxes of proton irradiation.

Toyohashi Tech researchers have fabricated Hall effect magnetic field sensors operable at least 400 C and in extreme radiation conditions using gallium nitride-based heterostructures with two-dimensional electron gas.

Notably, the AlGaIn/GaN micro-Hall sensors were stable up to at least 400 C, whereas sensors fabricated using the GaAs and InSb degraded from ~120 oC.

Silicon and III-V compound semiconductor Hall effect magnetic field sensors are widely used in the electronics industry for monitoring rotation in equipment such as optical memory disks and for banknote authentication in vending machines. However, the use of Hall sensors for monitoring magnetic fields in outer space and [nuclear power stations](#) is more challenging because of the large fluctuations in temperature and [harmful radiation](#) in these environments.



Variation of Hall voltage with magnetic field with drive current for an AlGaIn/GaN Hall sensor before and after irradiation with proton fluence of 10^{14} cm⁻². Credit: Toyohashi University of Technology

Furthermore, the [electron mobility](#) and two dimensional [electron density](#) of the AlGaIn/GaN micro-Hall sensors were only slightly affected by a 1×10^{13} cm⁻² proton dose at 380 keV.

The researchers are actively seeking industrial partners to exploit the robust properties of the 2DEG-AlGaIn/GaN 2DEG Hall sensors for operation at high temperatures and in harsh radiation environments.

A potential application included imaging of ferromagnetic domains at the surface of permanent magnetics. Adarsh Sandhu has demonstrated the imaging of magnetic domains in ferromagnetic materials with a AlGaIn/GaN micro-Hall sensor in a high temperature scanning Hall probe microscope (SHPM).

More information: 1. S. Koide, H. Takahashi, A Abderrahmane, I. Shibasaki, A.Sandhu, High Temperature Hall sensors using AlGaIn/GaN HEMT Structures, Institute of Physics Journal of Physics Conference Series (in press)

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Provided by Toyohashi University of Technology
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